

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP02590 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

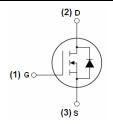
General Features

- $V_{DS} = 250V, I_{D} = 90A$ $R_{DS(ON)} < 15m\Omega @ V_{GS} = 10V$
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- Optimized body diode reverse recovery performance

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02590	NCEP02590	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	250	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	90	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	63.6	Α
Pulsed Drain Current	I _{DM}	360	Α
Maximum Power Dissipation	P _D	330	W
Derating factor		2.2	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	1700	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	R ₀ JC	0.45	°C/W	
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						•
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	250		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =45A	-	14.2	15	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =45A	70	-	-	S
Dynamic Characteristics (Note4)						•
Input Capacitance	C _{lss}	\/ -425\/\/ -0\/	-	6595	-	PF
Output Capacitance	C _{oss}	V_{DS} =125V, V_{GS} =0V, F=1.0MHz	-	409.5	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	11	-	PF
Switching Characteristics (Note 4)				'		•
Turn-on Delay Time	t _{d(on)}	V _{DD} =125V,I _D =45A V _{GS} =10V,R _G =4.7Ω	-	19.5	-	nS
Turn-on Rise Time	t _r		-	28	-	nS
Turn-Off Delay Time	t _{d(off)}		-	48	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Qg	\/ 405\/\ 45A	-	90.9		nC
Gate-Source Charge	Q _{gs}	V_{DS} =125 V , I_{D} =45 A ,	-	40.4		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	18		nC
Drain-Source Diode Characteristics			•			•
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =90A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	90	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 45A	-	186		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	_	1.35		uC

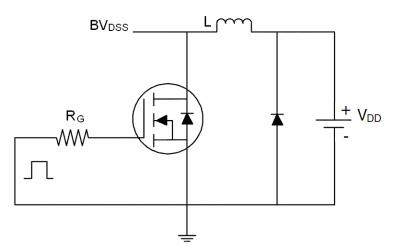
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

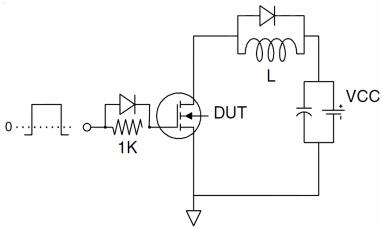


Test Circuit

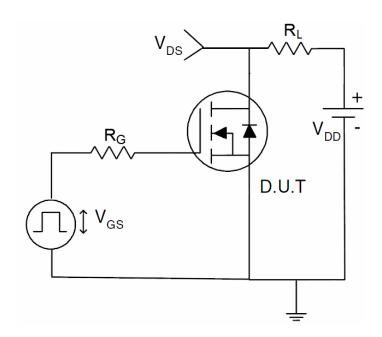
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit







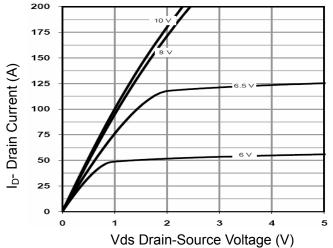


Figure 1 Output Characteristics

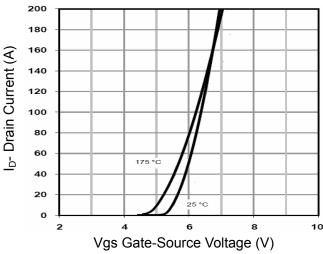


Figure 2 Transfer Characteristics

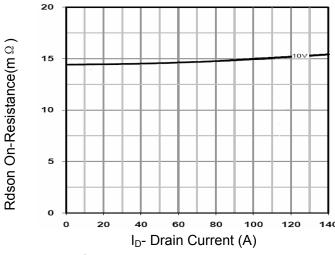


Figure 3 Rdson- Drain Current

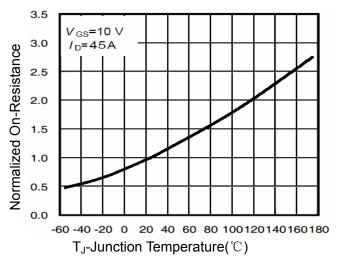


Figure 4 Rdson-JunctionTemperature

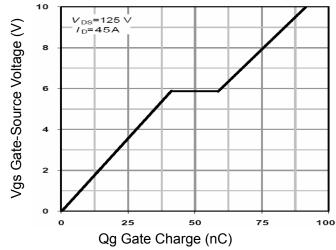


Figure 5 Gate Charge

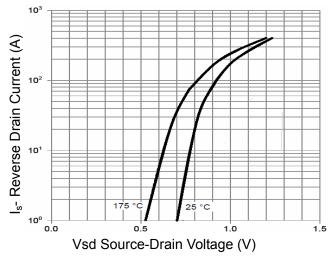


Figure 6 Source- Drain Diode Forward



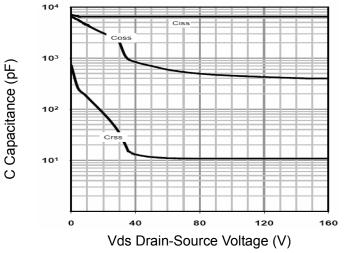


Figure 7 Capacitance vs Vds

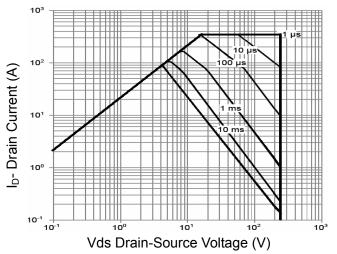


Figure 8 Safe Operation Area

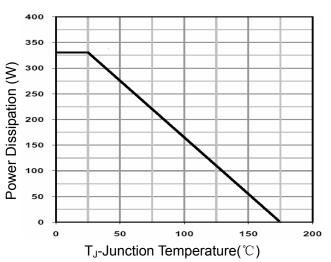


Figure 9 Power De-rating

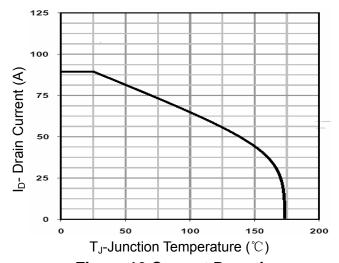


Figure 10 Current De-rating

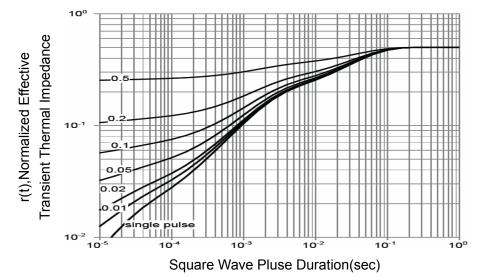
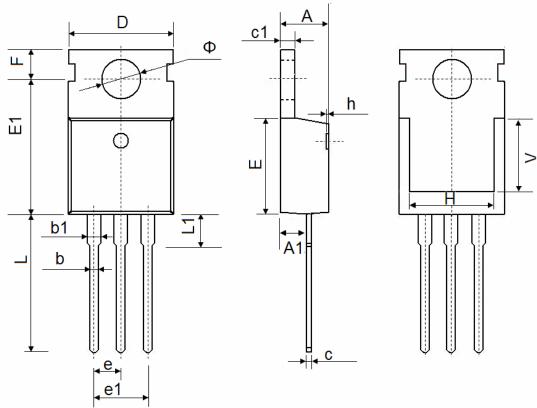


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220-3L Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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